NSN 5961-01-131-0260

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Inclosure Material:
Metal
Overall Length:
1.573 inches
Overall Height:
0.450 inches
Overall Width:
1.050 inches
End Application:
Lgm 30 81205
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case and quality assurance level txv
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
-80.0 collector to base voltage/static/emitter open and -80.0 collector to emitter voltage/static/base open and -15.0 emitter to base voltage
static, collector open
Current Rating Per Characteristic:
Between -15.00 amperes source cutoff current and -50.00 amperes source cutoff current
Power Rating Per Characteristic:
300.0 watts small-signal input power, common-collector preset
Special Features:
Junction pattern arrangement: pnp
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
1 case and 2 uninsulated wire lead
Specification Data:
81349-mil-s-19500/466 government specification
Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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